

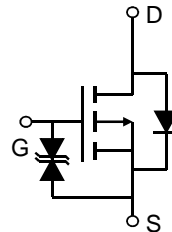
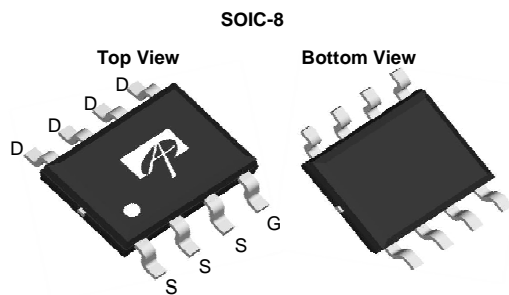
### General Description

The AO4423 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

### Product Summary

$V_{DS}$  (V) = -30V  
 $I_D$  = -17A  
 $R_{DS(ON)} < 6.2m\Omega$  ( $V_{GS} = -20V$ )  
 $R_{DS(ON)} < 7.2m\Omega$  ( $V_{GS} = -10V$ )

ESD Protected  
 100% UIS tested  
 100% Rg tested (note \*)



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current <sup>AF</sup>	$I_D$	-17	A
$T_A=25^\circ\text{C}$		-14	
$T_A=70^\circ\text{C}$			
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-182	
Power Dissipation <sup>A</sup>	$P_D$	3.1	W
$T_A=25^\circ\text{C}$		2	
$T_A=70^\circ\text{C}$			
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>AF</sup>	$R_{\theta JA}$	26	40	$^\circ\text{C/W}$
$t \leq 10s$				
Maximum Junction-to-Ambient <sup>A</sup>		50	75	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	14	24	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$ , $V_{GS}=0\text{V}$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			$\pm 1$	$\mu\text{A}$
		$V_{DS}=0\text{V}$ , $V_{GS}=\pm 25\text{V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=-250\mu\text{A}$	-1.5	-2.1	-2.6	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$ , $V_{DS}=-5\text{V}$	-182			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-20\text{V}$ , $I_D=-15\text{A}$ $T_J=125^\circ\text{C}$		5.1 7.4	6.2 9	$\text{m}\Omega$
		$V_{GS}=-10\text{V}$ , $I_D=-15\text{A}$		5.9	7.2	$\text{m}\Omega$
		$V_{GS}=-6\text{V}$ , $I_D=-10\text{A}$		7.5	9.5	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}$ , $I_D=-15\text{A}$		48		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}$ , $V_{GS}=0\text{V}$		-0.71	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-4.2	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=-15\text{V}$ , $f=1\text{MHz}$		2527	3033	pF
$C_{oss}$	Output Capacitance			583		pF
$C_{rss}$	Reverse Transfer Capacitance			397	556	pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$	2.1	4.3	6.4	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $I_D=-15\text{A}$		47	57	nC
$Q_{gs}$	Gate Source Charge			8		nC
$Q_{gd}$	Gate Drain Charge			14		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $R_L=1.0\Omega$ , $R_{GEN}=3\Omega$		12		ns
$t_r$	Turn-On Rise Time			8		ns
$t_{D(off)}$	Turn-Off DelayTime			54		ns
$t_f$	Turn-Off Fall Time			87		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-15\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		26.1	32	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-15\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		12.3		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

F: The current rating is based on the  $t \leq 10\text{s}$  junction to ambient thermal resistance rating.

Note \*: This device is guaranteed RG 100% tested after date code 8V11 (Jan 1st 2008)

Rev10: May. 2012

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## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

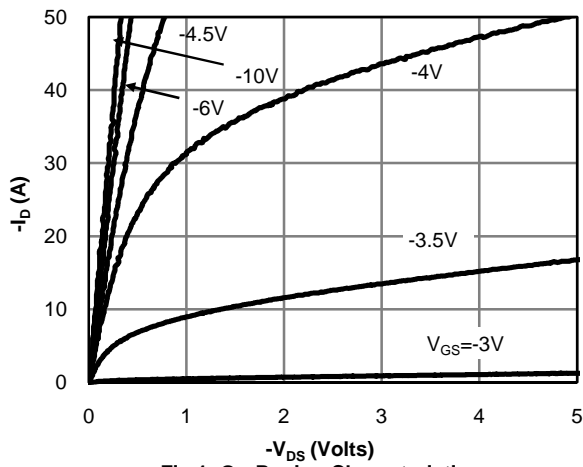


Fig 1: On-Region Characteristics

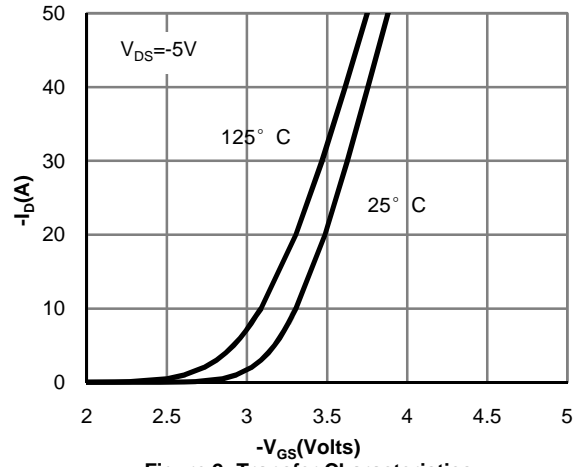


Figure 2: Transfer Characteristics

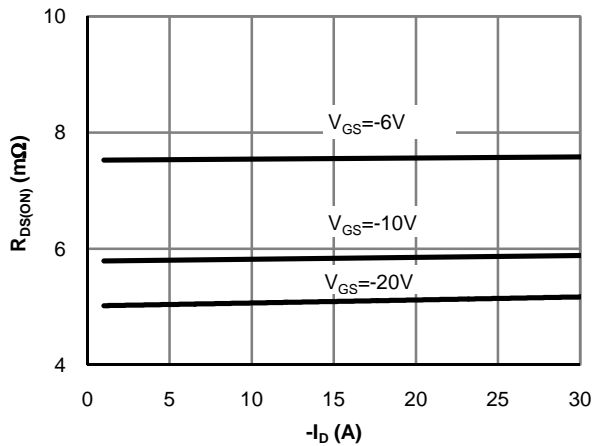


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

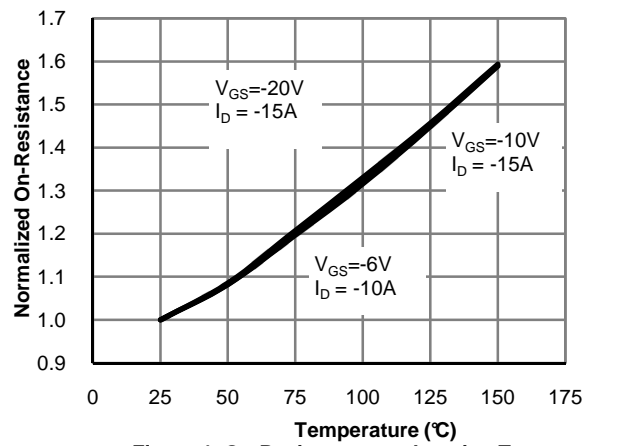


Figure 4: On-Resistance vs. Junction Temperature

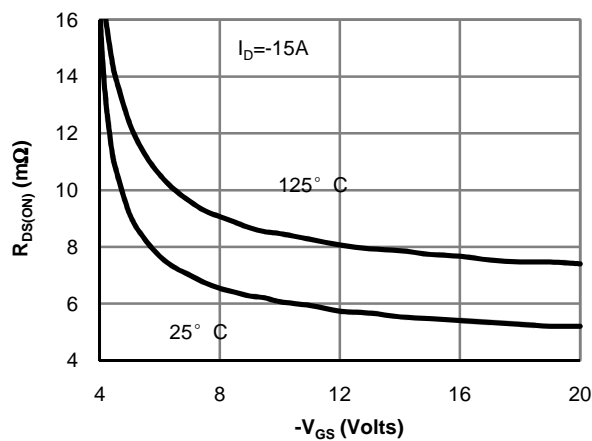


Figure 5: On-Resistance vs. Gate-Source Voltage

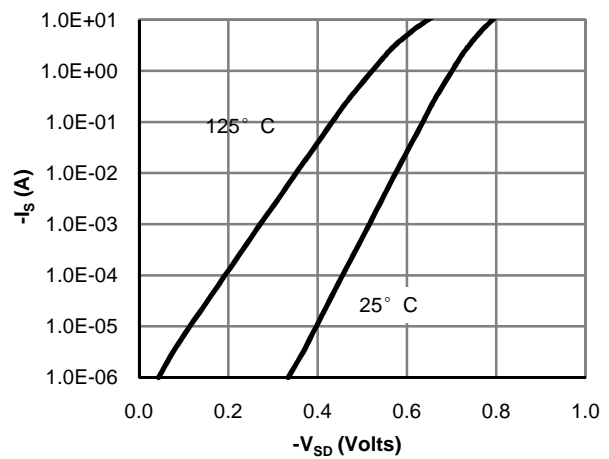


Figure 6: Body-Diode Characteristics

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